HF / VHF power LDMOS transistor

Rev. 3 — 1 September 2015



1. Product profile

1.1 General description

A 20 W LDMOS RF transistor for broadcast applications and industrial applications in the HF and VHF band.

Table 1. Production test performance

Mode of operation	f	V _{DS}	PL	G _p	η _D
	(MHz)	(V)	(W)	(dB)	(%)
CW	225	50	20	27.5	70

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical CW performance at frequency of 225 MHz, a supply voltage of 50 V and an I_{Dq} of 50 mA:
 - ◆ Average output power = 20 W
 - ◆ Power gain = 27.5 dB
 - ◆ Efficiency = 70 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate		1 ,⊢
3	source	[1] () 3	2 — 3 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLF571	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT467C	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	110	V
V_{GS}	gate-source voltage		-0.5	+11	V
I _D	drain current		-	3.6	Α
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 20 W	2.9	K/W

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6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.25 \text{ mA}$	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 25 mA	1.25	1.7	2.25	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 50 \text{ mA}$	1.25	1.75	2.25	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	3.0	3.6	-	Α
I _{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 1.25 A	-	1.8	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 833 \text{ mA}$	-	1.34	-	Ω
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	0.18	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	22.9	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	9.64	-	pF

Table 7. RF characteristics

Mode of operation: CW; f = 225 MHz; RF performance at $V_{DS} = 50$ V; $I_{Dq} = 50$ mA; $T_{case} = 25$ °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L} = 20 \text{ W}$	25.5	27.5	29.5	dB
RLin	input return loss	P _L = 20 W	10	13	-	dB
η_{D}	drain efficiency	P _L = 20 W	67	70	-	%

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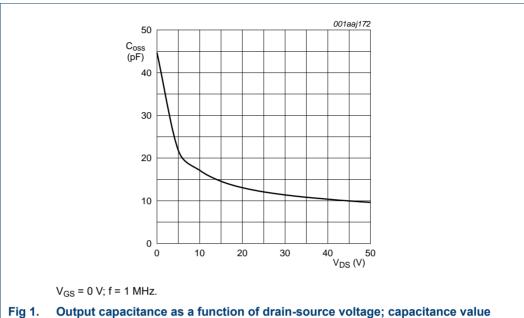


Fig 1. Output capacitance as a function of drain-source voltage; capacitance value without internal matching

6.1 Ruggedness in class-AB operation

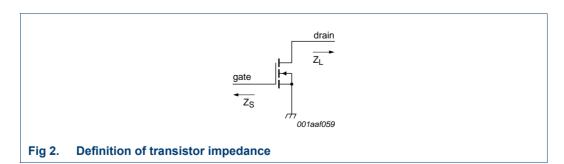
The BLF571 is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 50 mA; P_{L} = 20 W; f = 225 MHz.

7. Application information

7.1 Impedance information

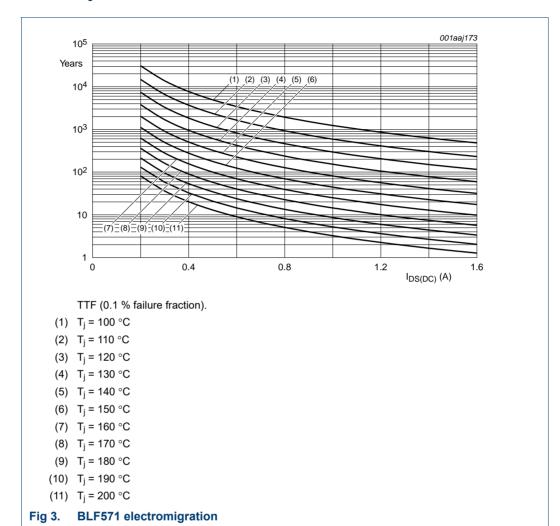
Table 8. Typical impedance Simulated Z_S and Z_L test circuit impedances.

	· ·	
f	Z _S	Z _L
MHz	Ω	Ω
225	9.7 + j31.5	31.7 + j29.3



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7.2 Reliability



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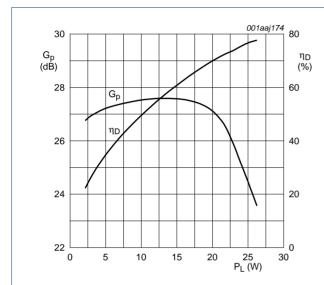
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8. Test information

8.1 RF performance

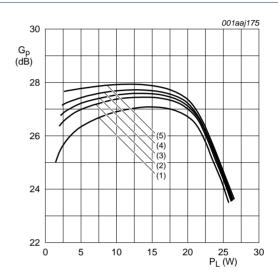
The following figures are measured in a class-AB production test circuit.

8.1.1 1-Tone CW



 $V_{DS} = 50 \text{ V}; I_{Dq} = 50 \text{ mA}; f = 225 \text{ MHz}.$



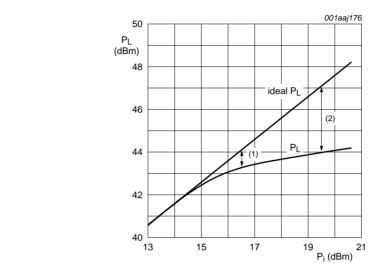


 $V_{DS} = 50 \text{ V}$; f = 225 MHz.

- (1) $I_{Dq} = 20 \text{ mA}$
- (2) $I_{Dq} = 40 \text{ mA}$
- (3) $I_{Dq} = 50 \text{ mA}$
- (4) $I_{Dq} = 60 \text{ mA}$
- (5) $I_{Dq} = 80 \text{ mA}$

Fig 5. Power gain as a function of load power; typical values

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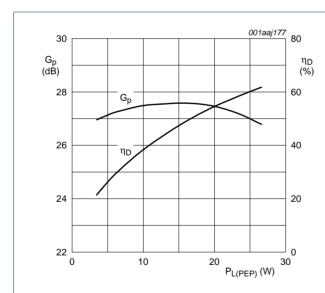


 $V_{DS} = 50 \text{ V}; I_{Dq} = 50 \text{ mA}; f = 225 \text{ MHz}.$

- (1) $P_{L(1dB)} = 43.3 \text{ dBm } (21.4 \text{ W})$
- (2) $P_{L(3dB)} = 44 \text{ dBm } (25.1 \text{ W})$

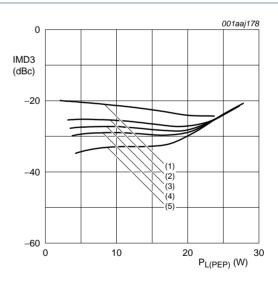
Fig 6. Load power as function of input power; typical values

8.1.2 2-Tone CW



 V_{DS} = 50 V; I_{Dq} = 50 mA; f_1 = 224.95 MHz; f_2 = 225.05 MHz.





 V_{DS} = 50 V; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

- (1) $I_{Dq} = 20 \text{ mA}$
- (2) $I_{Dq} = 40 \text{ mA}$
- (3) $I_{Dq} = 50 \text{ mA}$
- (4) $I_{Dq} = 60 \text{ mA}$
- (5) $I_{Dq} = 80 \text{ mA}$

Fig 8. Third order intermodulation distortion as a function of peak envelope load power; typical values

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8.2 Test circuit

Table 9. List of components

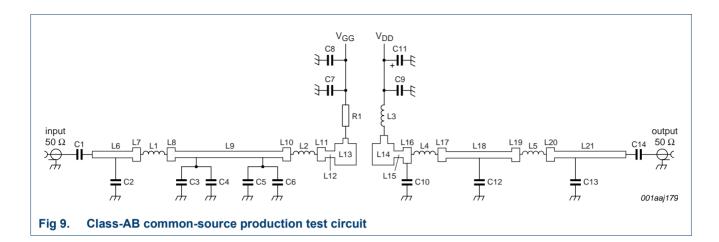
All capacitors should be soldered vertically. For test circuit, see Figure 9 and Figure 10.

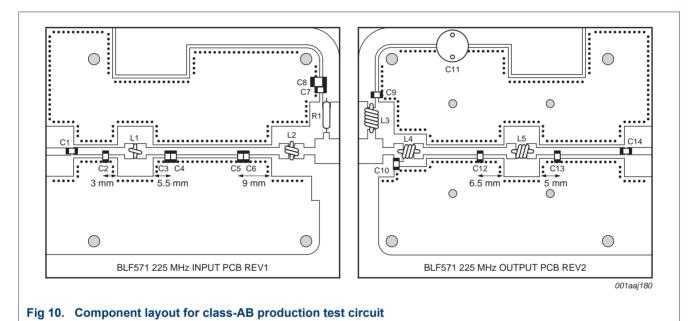
Component	Description	Value	Remarks
C1, C3, C4, C5, C14	multilayer ceramic chip capacitor	100 pF	Ш
C2	multilayer ceramic chip capacitor	39 pF	[1]
C6	multilayer ceramic chip capacitor	68 pF	[1]
C7, C9	multilayer ceramic chip capacitor	1 nF	[1]
C8	multilayer ceramic chip capacitor	4.7 μF	TDK C4532X7R1E475MT020U or equivalent
C10	multilayer ceramic chip capacitor	8.2 pF	[1]
C11	electrolytic capacitor	220 μF	
C12	multilayer ceramic chip capacitor	33 pF	[1]
C13	multilayer ceramic chip capacitor	15 pF	[1]
L1	1 turn enamelled copper wire	D = 5.5 mm; d = 1 mm; length = 1 mm	
L2	2 turns enamelled copper wire	D = 3.5 mm; d = 1 mm; length = 3 mm	
L3	5 turns enamelled copper wire	D = 6 mm; d = 1 mm; length = 5 mm	
L4	3.3 turns enamelled copper wire	D = 3 mm; d = 1 mm; length = 4 mm	
L5	3 turns enamelled copper wire	D = 3 mm; d = 1 mm; length = 3 mm	
L6	stripline	-	[2] (L × W) 16.5 mm × 2.4 mm
L7, L8, L10, L11, L17, L19, L20	stripline	-	[2] (L × W) 3.0 mm × 5.0 mm
L9	stripline	-	[2] (L × W) 43.0 mm × 2.4 mm
L12, L15	stripline	-	[2] (L × W) 3.5 mm × 2.4 mm
L13, L14	stripline	-	[2] (L × W) 8.0 mm × 8.0 mm
L16	stripline	-	[2] (L × W) 3.0 mm × 5.9 mm
L18	stripline	-	[2] (L × W) 27.0 mm × 2.4 mm
L21	stripline	-	[2] (L × W) 28.5 mm × 2.4 mm
R1	metal film resistor	1000 Ω; 0.6 W	

^[1] American Technical Ceramics type 100B or capacitor of same quality.

^[2] Printed-Circuit Board (PCB): Rogers 5880; ϵ_r = 2.2 F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.

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9. Package outline

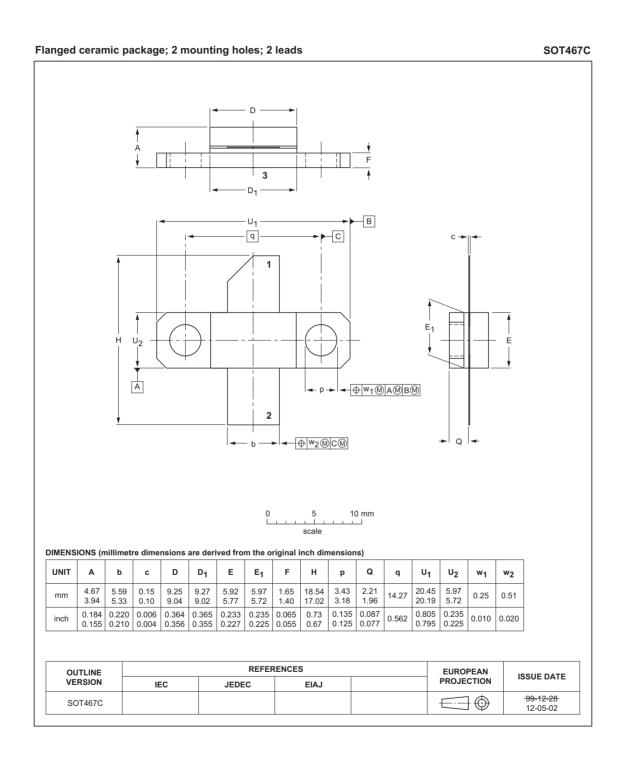


Fig 11. Package outline SOT467C

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10. Abbreviations

Table 10. Abbreviations

Acronym	Description
CW	Continuous Wave
EDGE	Enhanced Data rates for GSM Evolution
GSM	Global System for Mobile communications
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
TTF	Time To Failure
VHF	Very High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF571#3	20150901	Product data sheet	-	BLF571_2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF571_2	20090224 Product data sheet -		BLF571_1		
BLF571_1	20081211	Preliminary data sheet	-	-	

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12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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